

## PMN27UP

# 20 V, 5.7 A P-channel Trench MOSFET Rev. 1 — 13 July 2011

Product data sheet

### **Product profile**

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- 1.8 V R<sub>DSon</sub> rated
- Very fast switching

Trench MOSFET technology

### 1.3 Applications

- Relay driver
- High-speed line driver

- High-side load switch
- Switching circuits

#### 1.4 Quick reference data

Table 1. **Quick reference data** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	-5.7	Α
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$		-	27	32	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

### **Pinning information**

Table 2. **Pinning information** 

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	D- D- D-	
2	D	drain	<u> </u>	
3	G	gate		
4	S	source	1 12 13	
5	D	drain	SOT457 (TSOP6)	Ś
6	D	drain		017aaa094



### 20 V, 5.7 A P-channel Trench MOSFET

### 3. Ordering information

### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN27UP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

### 4. Marking

#### Table 4. Marking codes

Type number	Marking code
PMN27UP	ZU

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<u> </u>				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-5.7	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-3.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$		-	-23	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	540	mW
			<u>[1]</u>	-	1385	mW
		T <sub>sp</sub> = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-1.5	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 20 V, 5.7 A P-channel Trench MOSFET

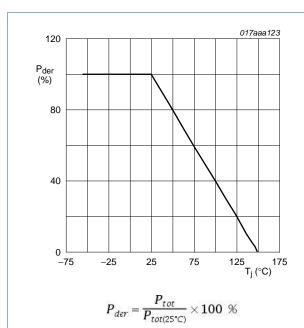


Fig 1. Normalized total power dissipation as a function of junction temperature

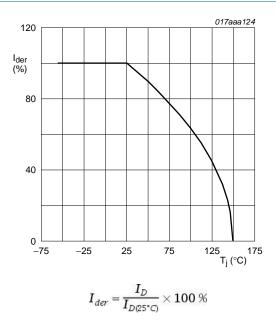
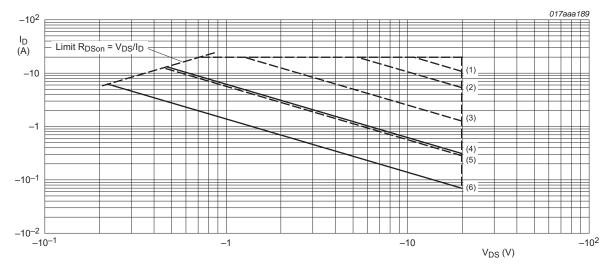


Fig 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> = single pulse

(1)  $t_p = 100 \, \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3)  $t_p = 10 \text{ ms}$ 

(4) DC;  $T_{sp} = 25$  °C

 $(5) t_p = 100 ms$ 

(6) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	200	230	K/W
	from junction to ambient		[2]	-	78	90	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	12	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

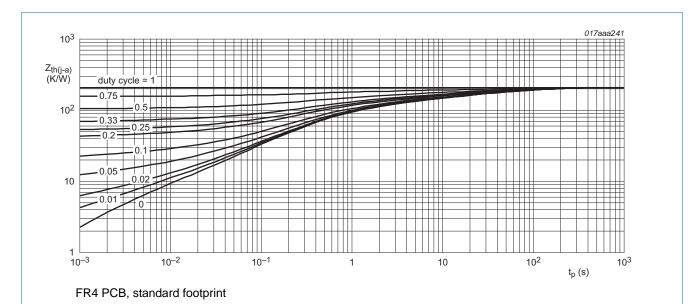
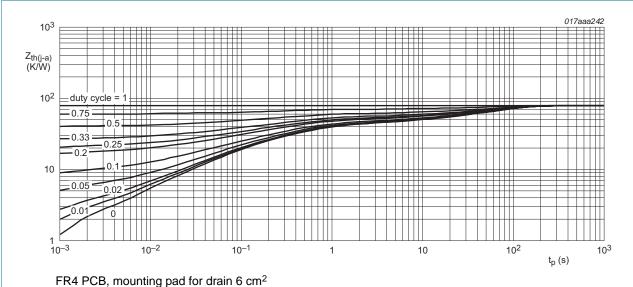


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig 5.

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### 20 V, 5.7 A P-channel Trench MOSFET

### 7. Characteristics

Table 7. Characteristics

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	27	32	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 150 \text{ °C}$	-	41	48	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2.0 \text{ A}; T_j = 25 \text{ °C}$	-	36	41	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.8 \text{ A}; T_j = 25 \text{ °C}$	-	57	66	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	14	-	S
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	21	31	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	4.2	-	nC
$Q_{GD}$	gate-drain charge		-	2.8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	2340	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	210	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	150	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ;	-	19	-	ns
t <sub>r</sub>	rise time	$T_j = 25 ^{\circ}\text{C};  I_D = -1 ^{\circ}\text{A}$	-	20	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	95	-	ns
t <sub>f</sub>	fall time		-	27	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -2.4 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_i = 25 \text{ °C}$	-	-0.75	-1	V

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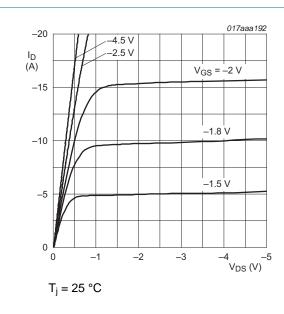
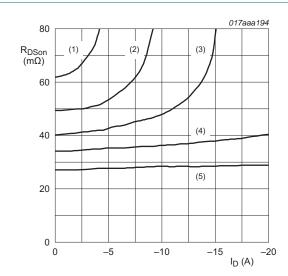


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = -1.5 \text{ V}$ 

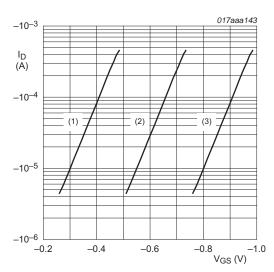
(2)  $V_{GS} = -1.8 \text{ V}$ 

(3)  $V_{GS} = -2.0 \text{ V}$ 

(4)  $V_{GS} = -2.5 \text{ V}$ 

(5)  $V_{GS} = -4.5 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



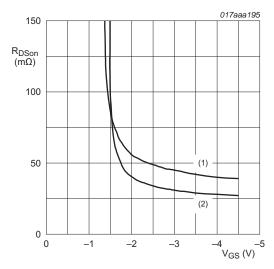
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -3 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



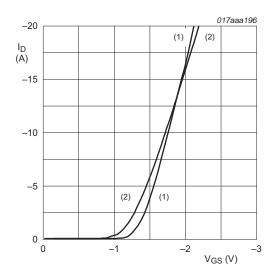
 $I_D = -2.4 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 20 V, 5.7 A P-channel Trench MOSFET

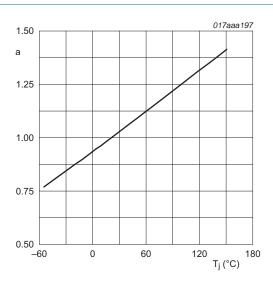


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

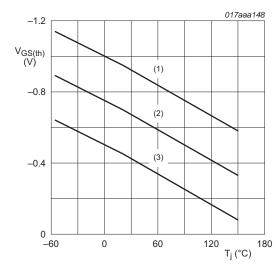
(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

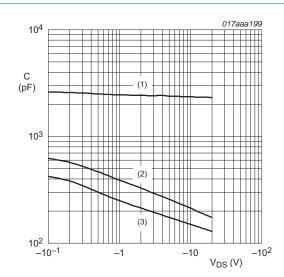
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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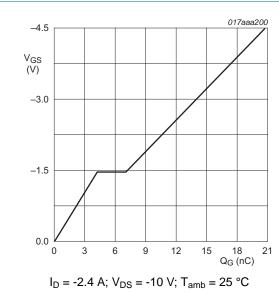


Fig 14. Gate-source voltage as a function of gate charge; typical values

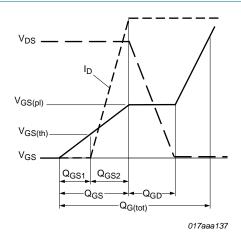
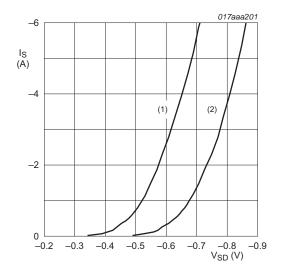


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

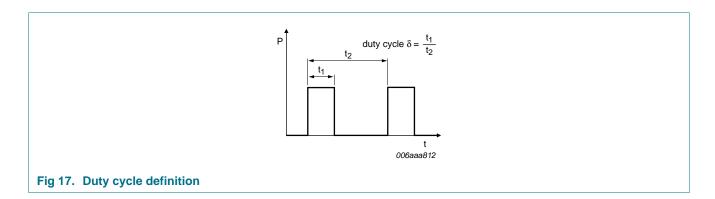
(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

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### 8. Test information



### 20 V, 5.7 A P-channel Trench MOSFET

### 9. Package outline

### Plastic surface-mounted package (TSOP6); 6 leads

**SOT457** 

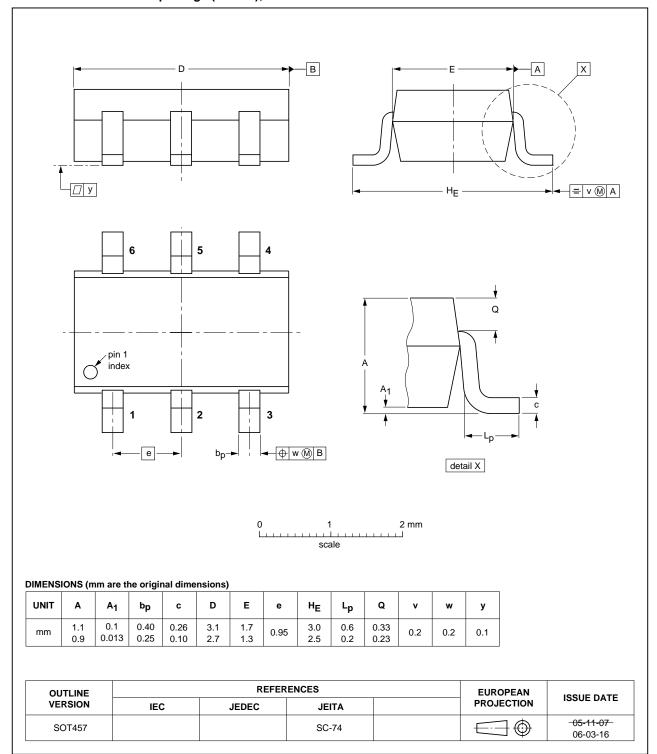
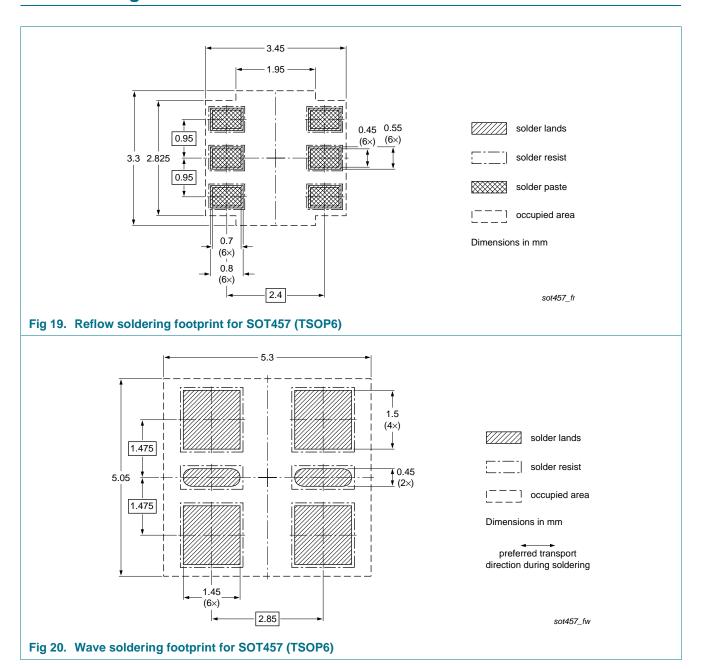


Fig 18. Package outline SOT457 (TSOP6)

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### 20 V, 5.7 A P-channel Trench MOSFET

### 10. Soldering



### 20 V, 5.7 A P-channel Trench MOSFET

### 11. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN27UP v.1	20110713	Product data sheet	-	-

#### 20 V, 5.7 A P-channel Trench MOSFET

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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